Rectifier diodes schottky barrier

PBYR1045F series

GENERAL DESCRIPTION

Low leakage, platinum barrier, schottky rectifier diodes in a full pack, plastic envelope featuring low forward voltage drop and absence of stored charge. These devices can withstand reverse voltage transients and have guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and zero switching losses are important.

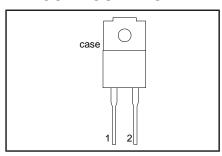
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{RRM}	PBYR10- Repetitive peak reverse voltage	35F 35	40F 40	45F 45	V
V _F I _{F(AV)}	Forward voltage Forward current	0.59 10	0.59 10	0.59 10	V A

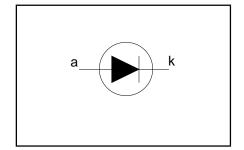
PINNING - SOD100

DESCRIPTION	
cathode	
anode	
isolated	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{hs} ≤ 125 °C	1 1 1	- 35 35 35 35	-40 40 40 40	-45 45 45 45	V V
I _{F(AV)}	Average forward current	square wave; δ = 0.5; T _{hs} ≤ 112 °C	-		10		Α
I _{F(RMS)}	RMS forward current	· ns — · · 2	_		14		Α
I _{FRM}	Repetitive peak forward current	t = 25 μs; δ = 0.5; T _{hs} ≤ 112 °C	-		20		A
I _{FSM}	Non-repetitive peak forward	t = 10 ms	-		100		Α
	current	t = 8.3 ms sinusoidal; $T_i = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RWM}(\text{max})}$	•		110		A
l ² t	I ² t for fusing	t = 10 ms	-		50		A ² s
I _{RRM}	Repetitive peak reverse current		-		1		Α
I _{RSM}	Non-repetitive peak reverse current	t _p = 100 μs	-		1		Α
T _{stg} T _j	Storage temperature Operating junction temperature		-65 -		175 150		သံ့

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ISOLATION

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from both terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	-	-	1500	V
C _{isol}	Capacitance from cathode to external heatsink	f = 1 MHz	-	12	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	with heatsink compound	-	-	5.5	K/W
R _{th j-a}		in free air.	-	55	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	I _F = 10 A; T _i = 125°C I _F = 20 A; T _i = 125°C	-	0.50	0.59	V
		$I_F = 20 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.62	0.75	V
		$I_{\rm F} = 20 {\rm A}$	-	0.78	0.87	V
I _R	Reverse current	$V_R = V_{RWM}$	-	50	100	μΑ
		$V_{R} = V_{RWM}; T_{i} = 125 ^{\circ}C$	-	13	26	mΑ
C _d	Junction capacitance	$V_R = V_{RWM}$; $T_j = 125 ^{\circ}C$ $f = 1MHz$; $V_R = 5V$; $T_j = 25 ^{\circ}C$ to	-	400	-	pF
		125 °C				

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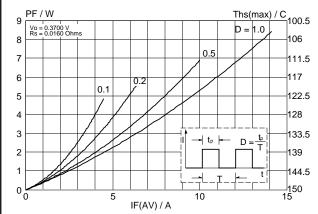


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

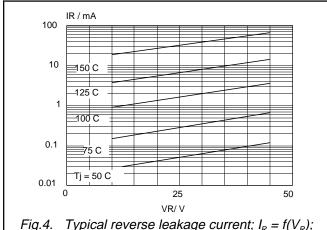


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter T_i

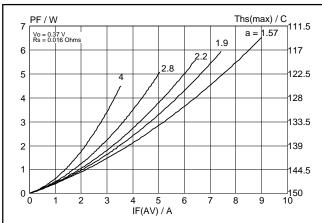


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = form factor = $I_{F(RMS)} / I_{F(AV)}$.

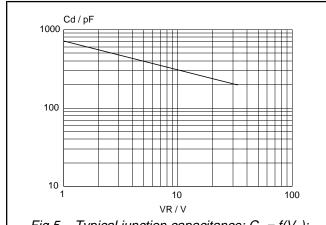


Fig.5. Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25^{\circ}$ C to 125° C.

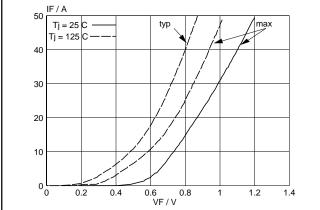


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

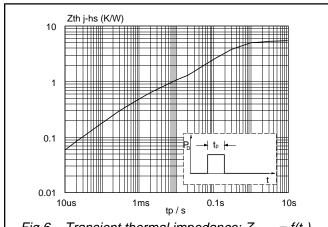
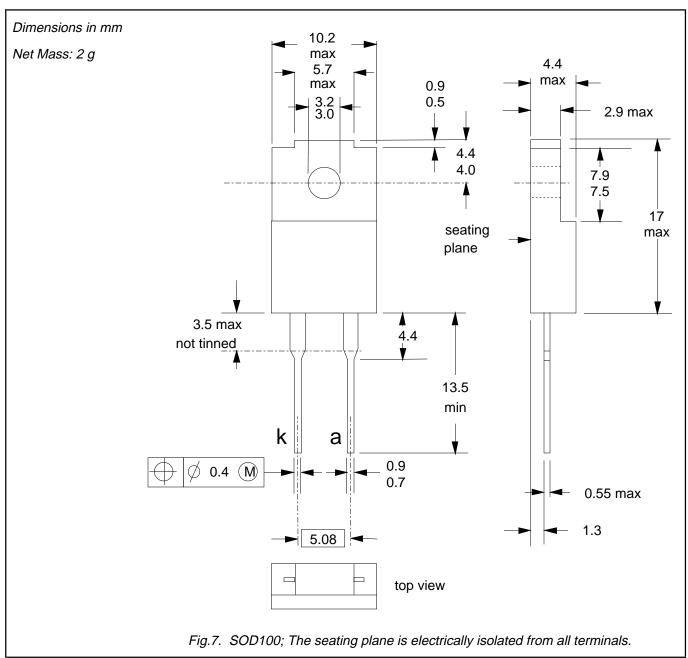


Fig.6. Transient thermal impedance; $Z_{th i-hs} = f(t_p)$.

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MECHANICAL DATA



- Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limitin arrealises				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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